

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments
1	BRS	L1	52	maleville-c\$.in.	USPA T; US-P GPUB ; EPO; JPO; DERW ENT; IBM_ TDB; USOC R	2004/08/10 13:41	
2	BRS	L2	0	tussot-c\$.in.	USPA T; US-P GPUB ; EPO; JPO; DERW ENT; IBM_ TDB; USOC R	2004/08/10 13:42	
3	BRS	L3	164270	(clean or cleaning or cleaned or cleaner or cleanse or cleansing or cleansed or cleanser or treat or treating or treated or treatment) adj10 (substrate or semiconductor or wafer or silicon or workpiece)	USPA T; US-P GPUB ; EPO; JPO; DERW ENT; IBM_ TDB; USOC R	2004/08/10 15:21	
4	BRS	L4	196919	(etch or etching or etched or etchant or strip or stripping or stripper or stripped) adj10 (substrate or semiconductor or wafer or silicon or workpiece)	USPA T; US-P GPUB ; EPO; JPO; DERW ENT; IBM_ TDB; USOC R	2004/08/10 15:23	

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments
5	BRS	L5	183836	HF or hydrofluoric or ammonium adj3 fluoride or "NH4F" or "NH4.sub.F"	USPAT; US-PGPUB; ; EPO; JPO; DERW ENT; IBM_ TDB; USOC R	2004/08/10 14:59	
6	BRS	L6	328869	13 or 14	USPAT; US-PGPUB; ; EPO; JPO; DERW ENT; IBM_ TDB; USOC R	2004/08/10 13:45	
7	BRS	L7	17556	16 same 15	USPAT; US-PGPUB; ; EPO; JPO; DERW ENT; IBM_ TDB; USOC R	2004/08/10 14:58	
8	BRS	L8	541	17 same (ozone or "O3" or "O.sub.3" or ozonized)	USPAT; US-PGPUB; ; EPO; JPO; DERW ENT; IBM_ TDB; USOC R	2004/08/10 15:11	

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments
9	BRS	L9	34	18 and (hydrophilic adj3 surface)	USPA T; US-P GPUB ; EPO; JPO; DERW ENT; IBM_ TDB; USOC R	2004/08/1 0 13:56	
10	BRS	L10	7	19 and (adhesion or adhesiv\$5)	USPA T; US-P GPUB ; EPO; JPO; DERW ENT; IBM_ TDB; USOC R	2004/08/1 0 13:52	
11	BRS	L11	67	18 and (hydrophilic)	USPA T; US-P GPUB ; EPO; JPO; DERW ENT; IBM_ TDB; USOC R	2004/08/1 0 13:58	
12	BRS	L12	48	111 and (silanol or oxide adj3 (layer or coating or film))	USPA T; US-P GPUB ; EPO; JPO; DERW ENT; IBM_ TDB; USOC R	2004/08/1 0 14:00	

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments
13	BRS	L13	4	l11 and (silanol or siloxane )	USPAT; US-PGPUB; ; EPO; JPO; DERWENT; IBM_TDB; USOCR	2004/08/10 14:02	
14	BRS	L14	1881	(form or forming or formed or formation) adj10 (siloxane\$ or "-Si-O-Si-" or "-Si-OH" or silanol) same (wafer or semiconductor or substrate or workpiece)	USPAT; US-PGPUB; ; EPO; JPO; DERWENT; IBM_TDB; USOCR	2004/08/10 14:49	
15	BRS	L15	85	l14 and 17	USPAT; US-PGPUB; ; EPO; JPO; DERWENT; IBM_TDB; USOCR	2004/08/10 14:04	
16	BRS	L16	11	l14 same 17	USPAT; US-PGPUB; ; EPO; JPO; DERWENT; IBM_TDB; USOCR	2004/08/10 14:04	

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments
17	BRS	L17	67	18 and hydrophilic	USPAT; US-PGPUB; ; EPO; JPO; DERWENT; IBM_TDB; USOCR	2004/08/10 14:49	
18	BRS	L18	5	(siloxane\$ or "-Si-O-Si-" or "-Si-OH" or silanol) and 117	USPAT; US-PGPUB; ; EPO; JPO; DERWENT; IBM_TDB; USOCR	2004/08/10 14:59	
19	BRS	L19	17100	16 same (hydrofluoric or "HF")	USPAT; US-PGPUB; ; EPO; JPO; DERWENT; IBM_TDB; USOCR	2004/08/10 15:24	
20	BRS	L20	953	119 same (ammonium adj3 fluoride or "NH4F" or "NH4.sub.F")	USPAT; US-PGPUB; ; EPO; JPO; DERWENT; IBM_TDB; USOCR	2004/08/10 15:24	

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments
21	BRS	L21	40	(siloxane\$ or "-Si-O-Si-" or "-Si-OH" or silanol) and 120	USPA T; US-P GPUB ; EPO; JPO; DERW ENT; IBM_ TDB; USOC R	2004/08/1 0 15:08	
22	BRS	L22	163	120 and (ozone or "O3" or "O.sub.3" or ozonized)	USPA T; US-P GPUB ; EPO; JPO; DERW ENT; IBM_ TDB; USOC R	2004/08/1 0 15:25	
23	BRS	L23	3	122 and (hydrogen-terminated adj3 surface)	USPA T; US-P GPUB ; EPO; JPO; DERW ENT; IBM_ TDB; USOC R	2004/08/1 0 15:12	
24	BRS	L24	22167 6	(134/\$ or 216/\$ or 438/\$).ccls.	USPA T; US-P GPUB ; EPO; JPO; DERW ENT; IBM_ TDB; USOC R	2004/08/1 0 15:15	

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments
25	BRS	L25	495	120 and 124	USPAT; US-PGPUB; ; EPO; JPO; DERWENT; IBM_TDB; USOCR	2004/08/10 15:15	
26	BRS	L26	20	120 same (ozone or "O3" or "O.sub.3" or ozonized)	USPAT; US-PGPUB; ; EPO; JPO; DERWENT; IBM_TDB; USOCR	2004/08/10 16:32	
27	BRS	L27	206662	(clean or cleaning or cleaned or cleaner or cleanse or cleansing or cleansed or cleanser or treat or treating or treated or treatment or immerse or immersion or immersing or immersed or dip or dipping or dipped or soak or soaking or soaked or spray or spraying or sprayed) adj10 (substrate or semiconductor or wafer or silicon or workpiece)	USPAT; US-PGPUB; ; EPO; JPO; DERWENT; IBM_TDB; USOCR	2004/08/10 15:23	

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments
28	BRS	L28	275	(decontaminate or decontaminating or decontaminated or decontamination) adj10 (substrate or semiconductor or wafer or silicon or workpiece)	USPA T; US-P GPUB ; EPO; JPO; DERW ENT; IBM_ TDB; USOC R	2004/08/10 15:23	
29	BRS	L29	365361	13 or 14 or 27 or 128	USPA T; US-P GPUB ; EPO; JPO; DERW ENT; IBM_ TDB; USOC R	2004/08/10 15:24	
30	BRS	L30	18108	129 same (hydrofluoric or "HF")	USPA T; US-P GPUB ; EPO; JPO; DERW ENT; IBM_ TDB; USOC R	2004/08/10 16:28	
31	BRS	L31	971	130 same (ammonium adj3 fluoride or "NH4F" or "NH4.sub.F")	USPA T; US-P GPUB ; EPO; JPO; DERW ENT; IBM_ TDB; USOC R	2004/08/10 15:25	



	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments
32	BRS	L32	165	l31 and (ozone or "O3" or "O.sub.3" or ozonized or ozone adj3 (gas or gaseous or vapor or vapour))	USPAT; US-PGPUB; ; EPO; JPO; DERW ENT; IBM_ TDB; USOC R	2004/08/10 15:48	
33	BRS	L33	20	l31 same (ozone or "O3" or "O.sub.3" or ozonized or ozone adj3 (gas or gaseous or vapor or vapour))	USPAT; US-PGPUB; ; EPO; JPO; DERW ENT; IBM_ TDB; USOC R	2004/08/10 15:40	
34	BRS	L34	0	JP2003218085.pn.	USPAT; US-PGPUB; ; EPO; JPO; DERW ENT; IBM_ TDB; USOC R	2004/08/10 15:40	
35	BRS	L35	88	l31 and (ozone or ozone adj3 (gas or gaseous or vapor or vapour))	USPAT; US-PGPUB; ; EPO; JPO; DERW ENT; IBM_ TDB; USOC R	2004/08/10 15:48	

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments
36	BRS	L36	71	135 and 124	USPA T; US-P GPUB ; EPO; JPO; DERW ENT; IBM_ TDB; USOC R	2004/08/10 15:48	
37	BRS	L37	3159	129 same (buffered adj "HF" or buffered adj hydrofluoric or "BOE" or buffered adj oxide adj etch)	USPA T; US-P GPUB ; EPO; JPO; DERW ENT; IBM_ TDB; USOC R	2004/08/10 16:31	
38	BRS	L38	48	137 same (ozone or "O3" or "O.sub.3" or ozonized)	USPA T; US-P GPUB ; EPO; JPO; DERW ENT; IBM_ TDB; USOC R	2004/08/10 16:32	
39	BRS	L39	31	138 and 124	USPA T; US-P GPUB ; EPO; JPO; DERW ENT; IBM_ TDB; USOC R	2004/08/10 16:32	